

Subir Parui

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7047652/publications.pdf>

Version: 2024-02-01

24
papers

582
citations

840776

11
h-index

642732

23
g-index

24
all docs

24
docs citations

24
times ranked

1159
citing authors

#	ARTICLE	IF	CITATIONS
1	Robust Spin Interconnect with Isotropic Spin Dynamics in Chemical Vapor Deposited Graphene Layers and Boundaries. ACS Nano, 2020, 14, 15864-15873.	14.6	12
2	Top dielectric induced ambipolarity in an n-channel dual-gated organic field effect transistor. Journal of Materials Chemistry C, 2019, 7, 10389-10393.	5.5	5
3	Molecular spectroscopy in a solid-state device. Materials Horizons, 2019, 6, 1663-1668.	12.2	7
4	Strain Effects on the Energy-Level Alignment at Metal/Organic Semiconductor Interfaces. ACS Applied Materials & Interfaces, 2019, 11, 12717-12722.	8.0	8
5	Hot Electrons and Hot Spins at Metal/Organic Interfaces. Advanced Functional Materials, 2018, 28, 1706105.	14.9	12
6	Gate-tunable graphene-organic interface barrier for vertical transistor and logic inverter. Applied Physics Letters, 2018, 113, .	3.3	7
7	Graphene as an electrode for solution-processed electron-transporting organic transistors. Nanoscale, 2017, 9, 10178-10185.	5.6	30
8	Energy Level Alignment at Metal/Solution-Processed Organic Semiconductor Interfaces. Advanced Materials, 2017, 29, 1606901.	21.0	37
9	A molecular spin-photovoltaic device. Science, 2017, 357, 677-680.	12.6	147
10	Frequency driven inversion of tunnel magnetoimpedance and observation of positive tunnel magnetocapacitance in magnetic tunnel junctions. Applied Physics Letters, 2016, 109, 052401.	3.3	10
11	Spin doping using transition metal phthalocyanine molecules. Nature Communications, 2016, 7, 13751.	12.8	30
12	Reliable determination of the Cu/n-Si Schottky barrier height by using in-device hot-electron spectroscopy. Applied Physics Letters, 2015, 107, .	3.3	8
13	Gate-Controlled Energy Barrier at a Graphene/Molecular Semiconductor Junction. Advanced Functional Materials, 2015, 25, 2972-2979.	14.9	58
14	Gate-tunable diode and photovoltaic effect in an organic/2D layered material p-n junction. Nanoscale, 2015, 7, 15442-15449.	5.6	84
15	Temperature dependent transport characteristics of graphene/n-Si diodes. Journal of Applied Physics, 2014, 116, .	2.5	53
16	Hot electron transport in a strongly correlated transition-metal oxide. Scientific Reports, 2013, 3, 1274.	3.3	16
17	Evidence of spin scattering and collection of hot electrons at different conduction minima in Si. Applied Physics Letters, 2013, 103, 082409.	3.3	2
18	Hot electron attenuation of direct and scattered carriers across an epitaxial Schottky interface. Journal of Physics Condensed Matter, 2013, 25, 445005.	1.8	3

#	ARTICLE	IF	CITATIONS
19	Probing electron transport across a LSMO/Nb:STO heterointerface at the nanoscale. Physical Review B, 2013, 87, .	3.2	17
20	Probing hot electron transport across an epitaxial Schottky interface of SrRuO ₃ /Nb:SrTiO ₃ . Applied Physics Letters, 2013, 102, .	3.3	8
21	Spin transport in metal and oxide devices at the nanoscale. , 2012, , .		1
22	Comparison of hot-electron transmission in ferromagnetic Ni on epitaxial and polycrystalline Schottky interfaces. Physical Review B, 2012, 85, .	3.2	7
23	Nanoscale hot electron transport across Cu/nâ€Si(100) and Cu/nâ€Si(111) interfaces. Physica Status Solidi - Rapid Research Letters, 2011, 5, 388-390.	2.4	10
24	Hot electron transmission in metals using epitaxial NiSi ₂ /n-Si(111) interfaces. Applied Physics Letters, 2011, 99, 032104.	3.3	10